

DATA SHEET

NEC

MOS FIELD EFFECT TRANSISTOR

2SK4092

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4092 is N-channel MOS FET device that features a low gate charge and excellent switching characteristics, and designed for high voltage applications such as switching power supply, AC adapter.

FEATURES

- Low on-state resistance
 $R_{DS(on)} = 0.4 \Omega$ MAX. ($V_{GS} = 10 V$, $I_D = 10 A$)
- Low gate charge
 $Q_G = 50$ nC TYP. ($V_{DD} = 450 V$, $V_{GS} = 10 V$, $I_D = 21 A$)
- Gate voltage rating: $\pm 30 V$
- Avalanche capability ratings

ORDERING INFORMATION

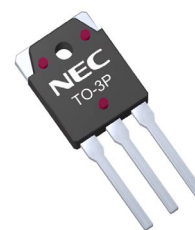
PART NUMBER	LEAD PLATING	PACKING	PACKAGE
2SK4092-A ^{Note}	Sn-Ag-Cu	100 p/package	TO-3P (MP-88) typ. 5.0 g

Note Pb-free (This product does not contain Pb in the external electrode and other parts.)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$)

Drain to Source Voltage ($V_{GS} = 0 V$)	V_{DSS}	600	V
Gate to Source Voltage ($V_{DS} = 0 V$)	V_{GSS}	± 30	V
Drain Current (DC) ($T_C = 25^\circ C$)	$I_{D(DC)}$	± 21	A
Drain Current (pulse) ^{Note1}	$I_{D(pulse)}$	± 60	A
Total Power Dissipation ($T_C = 25^\circ C$)	P_{T1}	200	W
Total Power Dissipation ($T_A = 25^\circ C$)	P_{T2}	3	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to +150	$^\circ C$
Single Avalanche Current ^{Note2}	I_{AS}	21	A
Single Avalanche Energy ^{Note2}	E_{AS}	29.4	mJ

(TO-3P)



Notes 1. $PW \leq 10 \mu s$, Duty Cycle $\leq 1\%$

2. Starting $T_{ch} = 25^\circ C$, $V_{DD} = 150 V$, $R_G = 25 \Omega$, $V_{GS} = 20 \rightarrow 0 V$

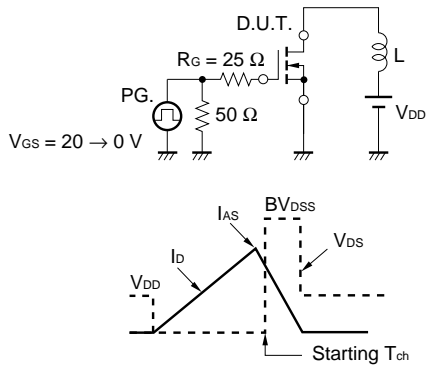
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

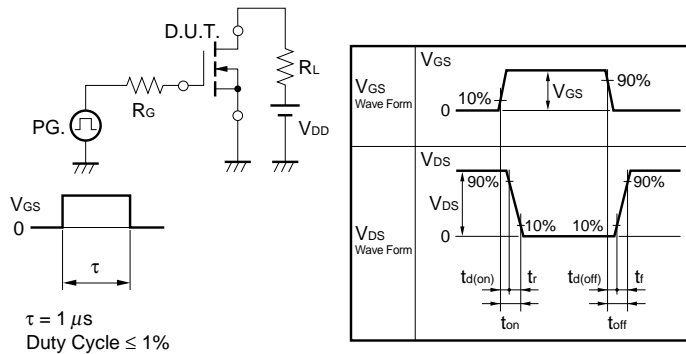
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±30 V, V _{DS} = 0 V			±100	nA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5	3.0	3.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 10 A	4.0			S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		0.34	0.4	Ω
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V,		3240		pF
Output Capacitance	C _{oss}	f = 1 MHz		550		pF
Reverse Transfer Capacitance	C _{rss}			3		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 150 V, I _D = 10 A,		38		ns
Rise Time	t _r	V _{GS} = 10 V,		15		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		58		ns
Fall Time	t _f			12		ns
Total Gate Charge	Q _G	V _{DD} = 450 V,		50		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 10 V,		24		nC
Gate to Drain Charge	Q _{GD}	I _D = 21 A		17		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 21 A, V _{GS} = 0 V		0.9	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 21 A, V _{GS} = 0 V,		480		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		6000		nC

Note Pulsed

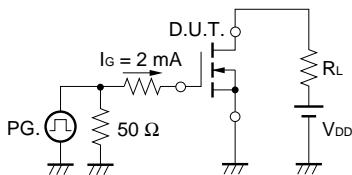
TEST CIRCUIT 1 AVALANCHE CAPABILITY



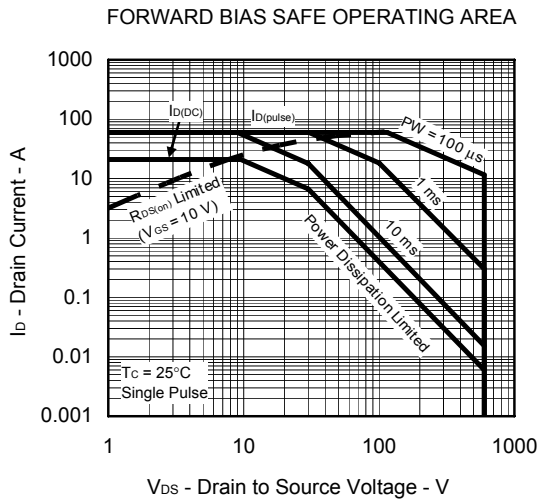
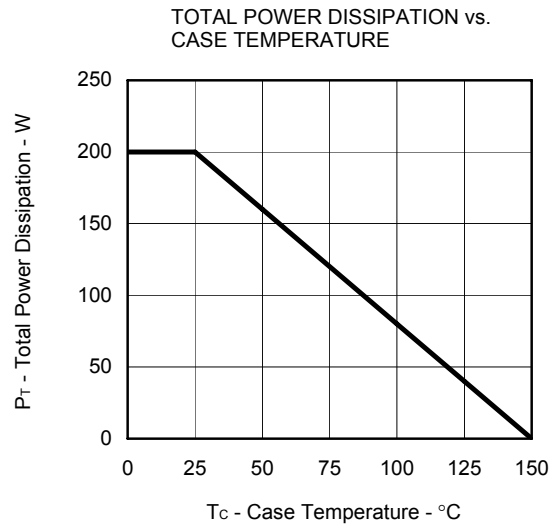
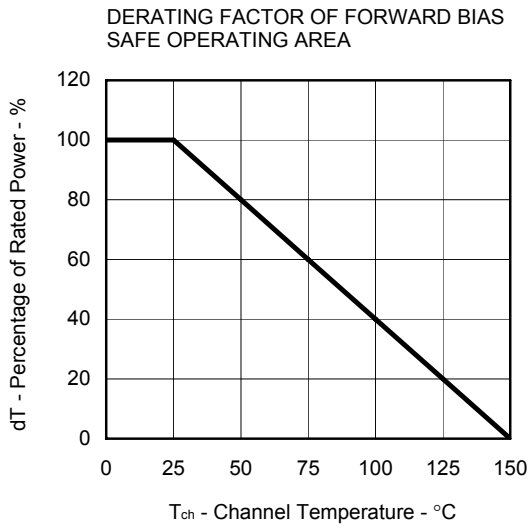
TEST CIRCUIT 2 SWITCHING TIME



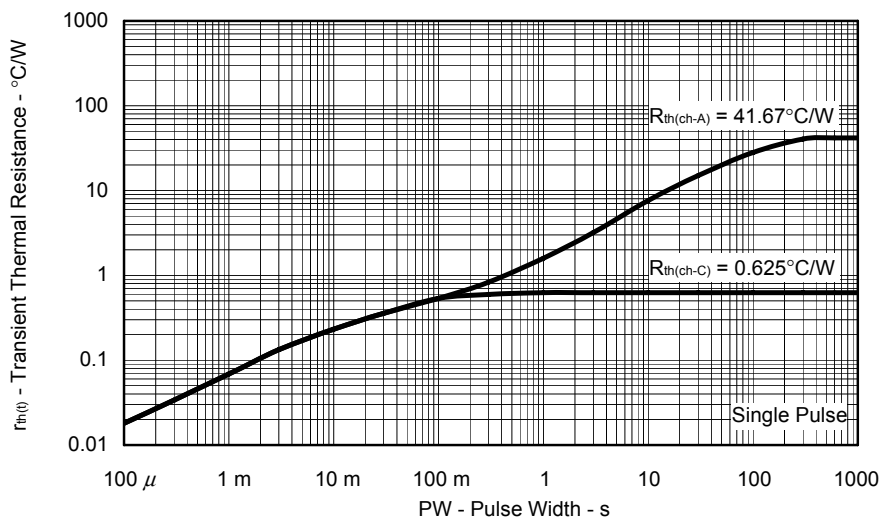
TEST CIRCUIT 3 GATE CHARGE



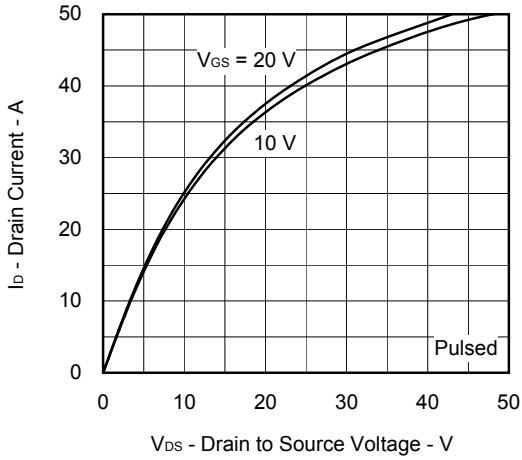
TYPICAL CHARACTERISTICS (T_A = 25°C)



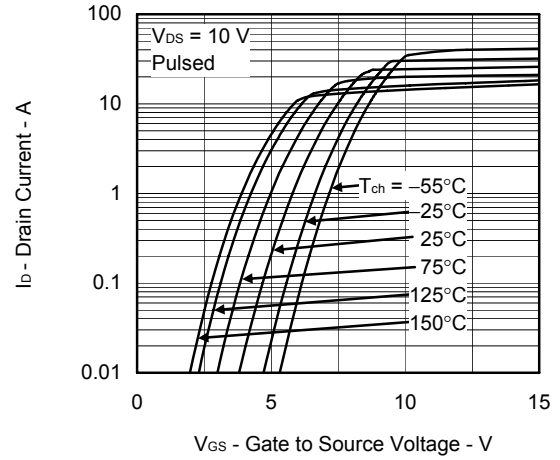
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



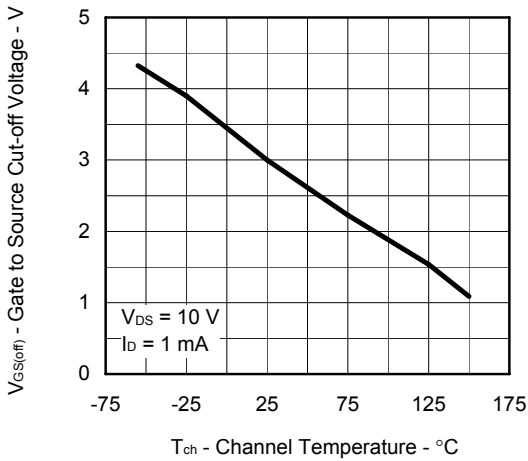
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



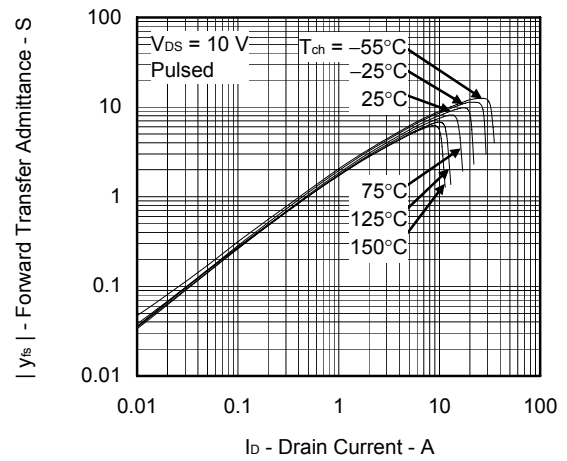
FORWARD TRANSFER CHARACTERISTICS



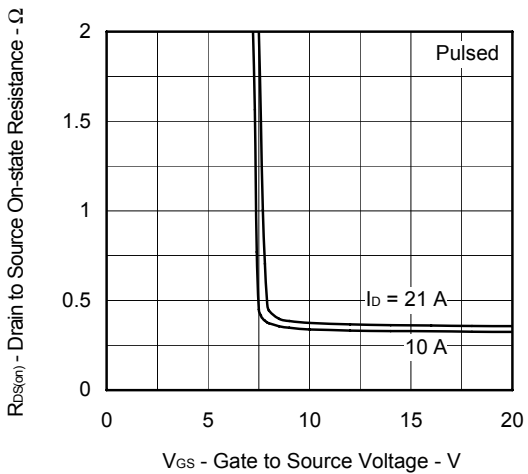
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



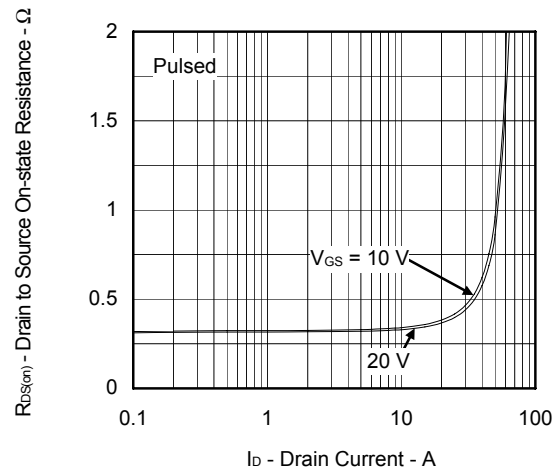
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



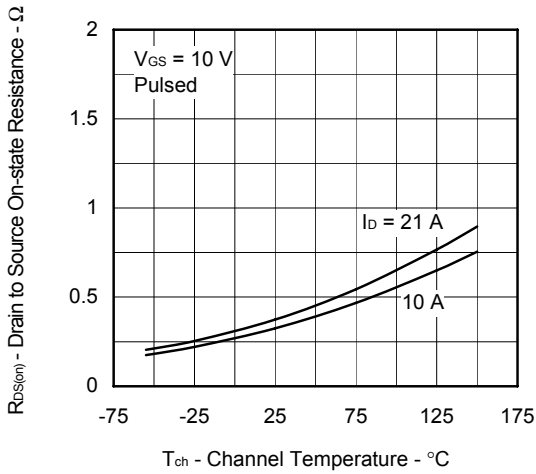
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



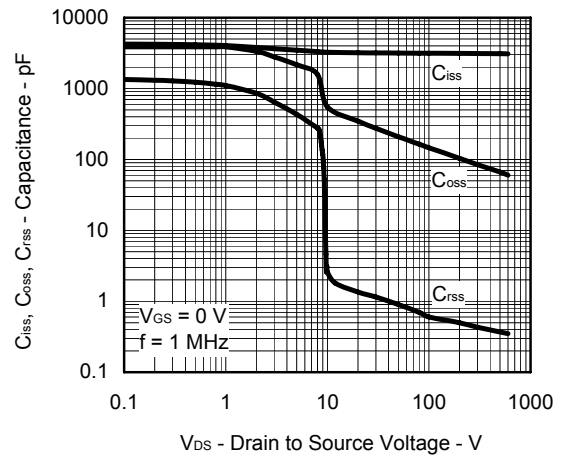
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



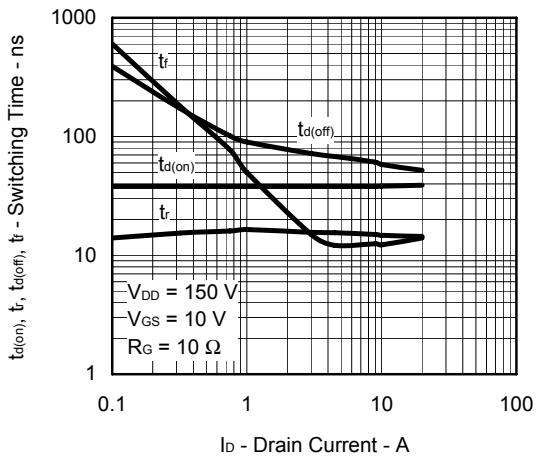
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



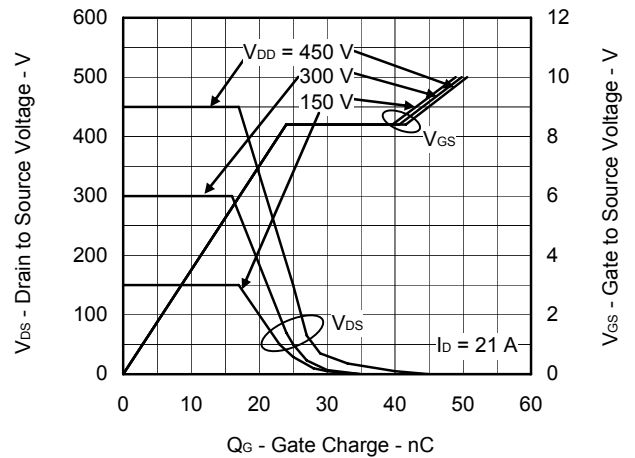
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



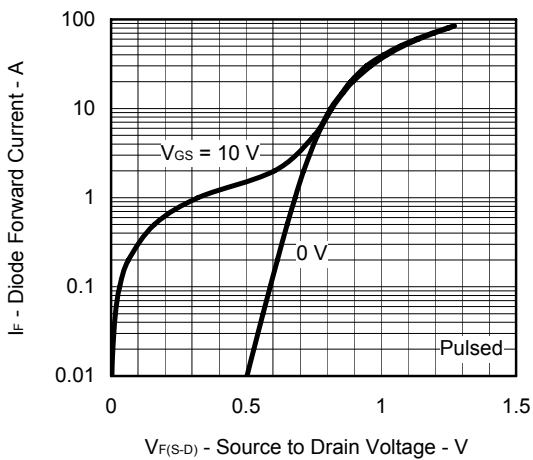
SWITCHING CHARACTERISTICS



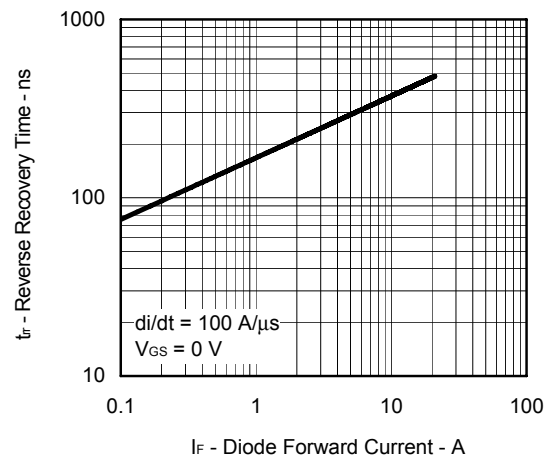
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



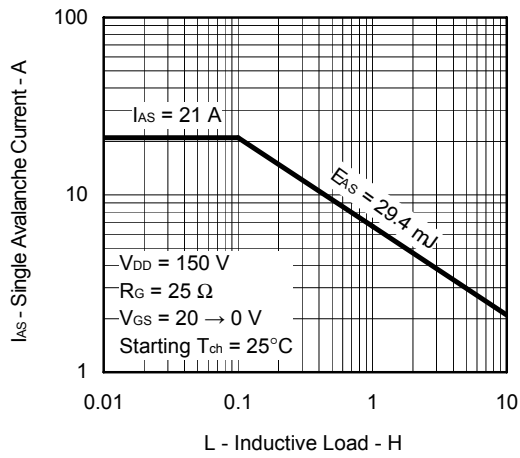
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



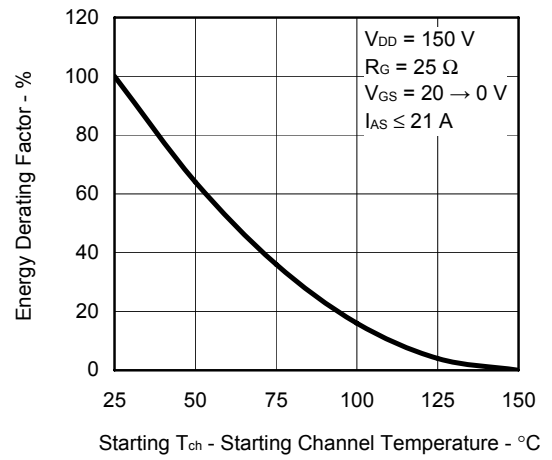
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs. INDUCTIVE LOAD

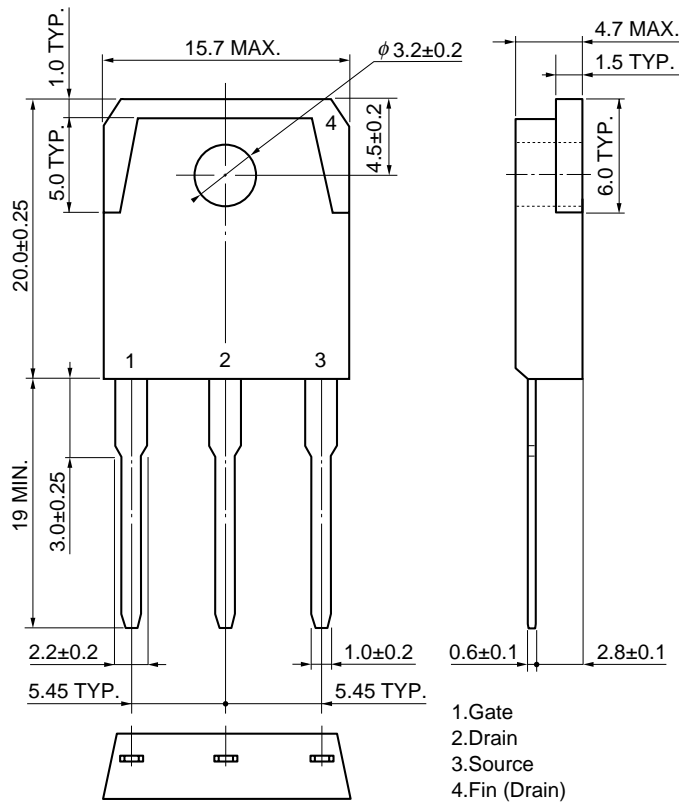


SINGLE AVALANCHE ENERGY DERATING FACTOR

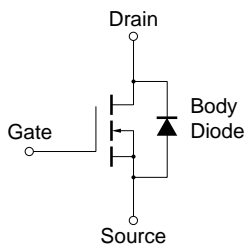


PACKAGE DRAWING (Unit: mm)

TO-3P (MP-88)



EQUIVALENT CIRCUIT



Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

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